

PVD

- ◆ DC source and RF Bias sputtering effect improved step coverage
- ◆ Pedestal available either in watercool Pedestal and Electrostatic Chuck with backside purge cooling
- ◆ Various deposition materials (Au / AlCu / Ti / Cu / TiW / NiV / Ag)
- ◆ Optional APC function
- ◆ Easy swap process kits with extended PM cycle time

Pre-Clean Etching

- ◆ Designed for high outgas organic substrate, PI, PBO, PR, Molding compound
- ◆ Wafer chuck supports warpage wafer
- ◆ Backside purge cooling system with chuck cooling down to -25°C
- ◆ Special designed kits enhanced MTBC from pre-clean by-product, a typical MTBC is > 8000 wafers
- ◆ No Aluminum Pasting needed
- ◆ Reactive processing with O₂ is an option
- ◆ Large turbo pump for effective outgas evacuation

Degas Chamber

- ◆ Multi wafers degas simultaneously offers extended process time
- ◆ Individual wafer temperature control system for various temperature settings and substrates
- ◆ Fast temperature ramping with lamp heating, >180°C/min
- ◆ Ultra high vacuum system with 250mm pumping port turbo pump and Water / Cryo pump
- ◆ Capable to handle organic and water outgas
- ◆ Molding compound, Low Temp. PI, PBO, PR, and Open Cavity

High Thru-put Mainframe

- ◆ Bridge tool capability for 200mm and 300mm
- ◆ Chamber design for fast size conversion
- ◆ Automatic Wafer Centering corrects wafer position
- ◆ Six equivalent SEMI standard interface for all types of process chambers including PVD, Pre-clean Etch, and Batch Degas
- ◆ Ultra short wafer swap time robot for high speed wafer thru-put
- ◆ Warpage substrate handle
- ◆ 4 buffer stations in transfer module offer extra time of cool down, outgas evacuation, and buffer slots
- ◆ Full function of CIM including FDC, PM, RMS...